

applying a plating voltage to the substrate once the substrate has been immersed into the electrolyte solution, the plating voltage being higher than the initial portion of the first biasing voltage.

86. (New) The method of claim 85, wherein the first biasing voltage is a ramping voltage.

87. (New) The method of claim 85, wherein the first biasing voltage increases from about zero volt to a range of about 1 volt to about 5 volts.

88. (New) The method of claim 85, wherein the first biasing voltage is configured to limit etching by the electrolyte solution of a seed layer disposed on the one or more features formed on the substrate.

89. (New) The method of claim 85, wherein the first biasing voltage is applied for about 0.125 second to about 1 second.

90. (New) The method of claim 85, wherein the first biasing voltage increases from about zero volt to a range of about 1 volt to about 5 volts in a period of about 0.125 second to about 1 second.

91. (New) The method of claim 85, wherein the electrolyte solution is acidic.

92. (New) The method of claim 85, wherein applying the plating voltage step comprises applying a pulsed biasing voltage to the substrate.

93. (New) The method of claim 92, wherein applying the pulsed biasing voltage comprises applying a positive plating current alternated with a negative de-plating current, the positive plating current being configured to cause deposition of metal inside the features, the negative de-plating current being configured to keep each opening of

the features open while the metal is being deposited inside the features by the positive plating current.

94. (New) The method of claim 85, further comprising applying a second biasing voltage to the substrate after applying the first biasing voltage and prior to applying the plating voltage, the second biasing voltage being configured to attract metal ions contained in the electrolyte solution near the features.

95. (New) The method of claim 85, wherein the second biasing voltage is higher than the plating voltage.

96. (New) The method of claim 85, wherein the first biasing voltage is a ramping voltage, and wherein applying the plating voltage step comprises applying a pulsed biasing voltage to the substrate.

97. (New) The method of claim 96, wherein applying the pulsed biasing voltage comprises applying a positive plating current alternated with a negative de-plating current, the positive plating current being configured to cause deposition of metal inside the features, the negative de-plating current being configured to keep each opening of the features open while the metal is being deposited inside the features by the positive plating current.

#### REMARKS

Applicants request entry and consideration of the above noted amendments prior to examination. New claims 85-97 have been added to more clearly recite aspects of the claimed invention. No new matter has been introduced by the new claims presented herein. The new claims have been made in a good faith effort to advance the prosecution on the merits. Please reconsider the claims pending in the application.